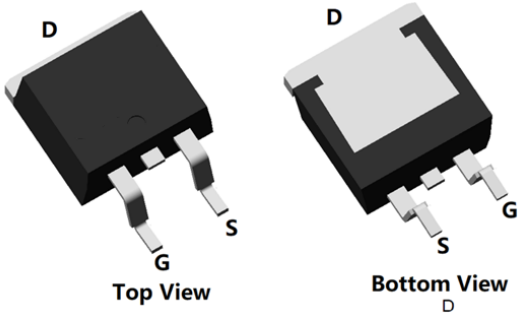
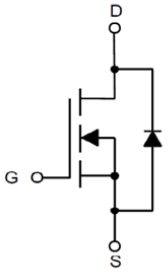
N-Channel Enhancement Mode Field Effect Transistor



TO-263



Product Summary

- V_{DS} 100V
- I_D 95A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜6.2mΩ
- 100% EAS Tested
- 100% ▽V_{DS} Tested
- ESD Level(HBM) Class 1C

General Description

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PD SR-MOS
- Uninterruptible power supply
- Battery management

■ Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V_{DS}	-	100	V
Gate-source Voltage			V_{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25℃,V_{GS}=10V	I_D	-	17	A
		T_A=100℃,V_{GS}=10V		-	11	
Continuous Drain Current (Note 1,3)	Steady-State	T_C=25℃,V_{GS}=10V,Chip limitation		-	95	
		T_C=100℃,V_{GS}=10V		-	60	
Pulsed Drain Current	T_C=25℃,t_p≤10μs		I_{DM}	-	380	
Maximum Body-Diode Continuous Current	T_C=25℃		I_S		85	
Avalanche energy (non-repetitive)	T_J=25℃,V_G=10V,R_G=25Ω,L=0.5mH,I_{AS}=26A		EAS	-	169	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25℃	P_D	-	3.4	W
		T_A=100℃		-	1.3	
Total Power Dissipation (Note 1,3)	Steady-State	T_C=25℃		-	102	
		T_C=100℃		-	41	
Junction and Storage Temperature Range			T_J ,T_{STG}	-55	150	℃

■Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	36	℃/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	1.22	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
B6D2G10H	F1	B6D2G10H	800	/	8000	13“ reel

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=1mA,Tj=25℃	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V,Tj=25℃	-	-	1	μA
		V_{DS}=80V,V_{GS}=0V,Tj=125℃	-	-	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V,Tj=25℃	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA,Tj=25℃	2	2.6	3.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=50A,Tj=25℃	-	4.7	6.2	mΩ
Diode Forward Voltage	V_{SD}	I_S=50A,V_{GS}=0V,Tj=25℃	-	0.92	1.2	V
Gate Resistance	R_G	f=1MHz,Tj=25℃	-	1.4	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V,f=1MHz,Tj=25℃	-	2090	-	pF
Output Capacitance	C_{oss}		-	1045	-	
Reverse Transfer Capacitance	C_{rss}		-	25	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=50V,I_D=50A,Tj=25℃	-	35.8	-	nC
Gate-Source Charge	Q_{gs}		-	9.7	-	
Gate-Drain Charge	Q_{gd}		-	10.7	-	
Reverse Recovery Charge	Q_{rr}	I_F=50A,di/dt=100A/μs,V_{GS}=0V, V_R=50V,Tj=25℃	-	29	-	nC
Reverse Recovery Time	t_{rr}		-	32	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=50V,I_D=50A,R_{GEN}=3Ω, Tj=25℃	-	13.4	-	ns
Turn-on Rise Time	t_r		-	45	-	
Turn-off Delay Time	$t_{D(off)}$		-	27	-	
Turn-off Fall Time	t_f		-	13.4	-	

Note：

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in^2 pad of 2oz. Copper, in the still air environment with T_A=25℃.The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).

■Typical Electrical and Thermal Characteristics Diagrams

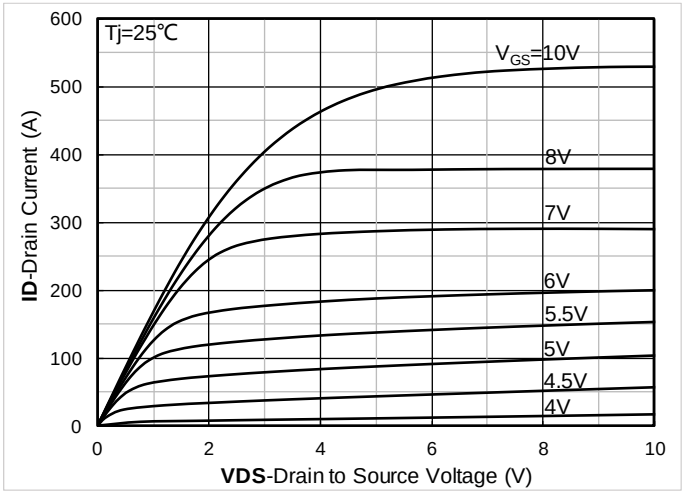


Figure 1. Output Characteristics; typical values

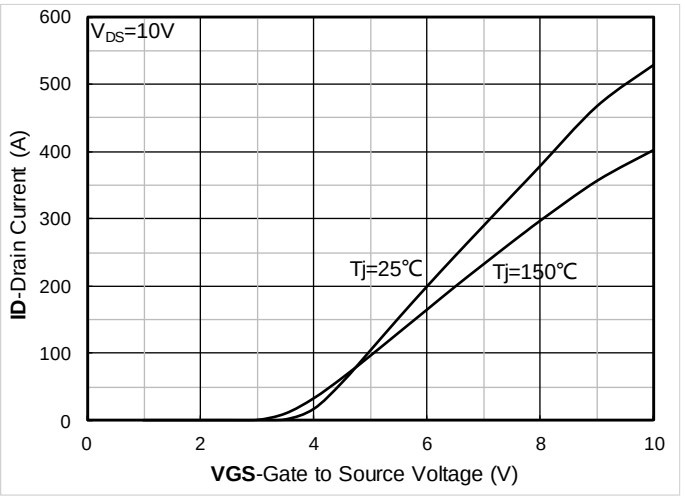


Figure 2. Transfer Characteristics; typical values

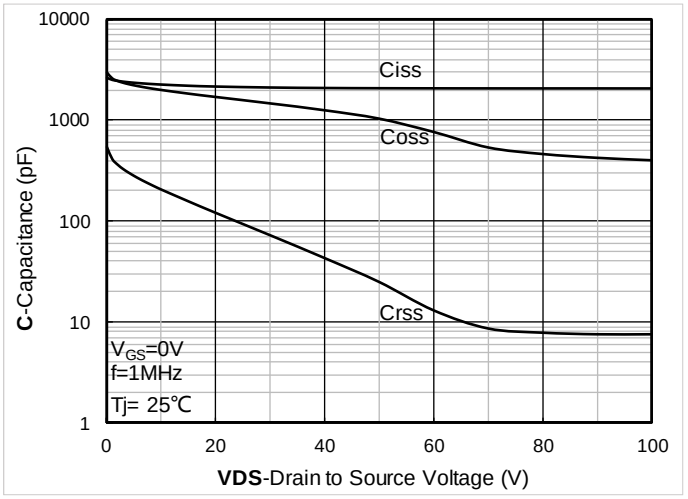


Figure 3. Capacitance Characteristics; typical values

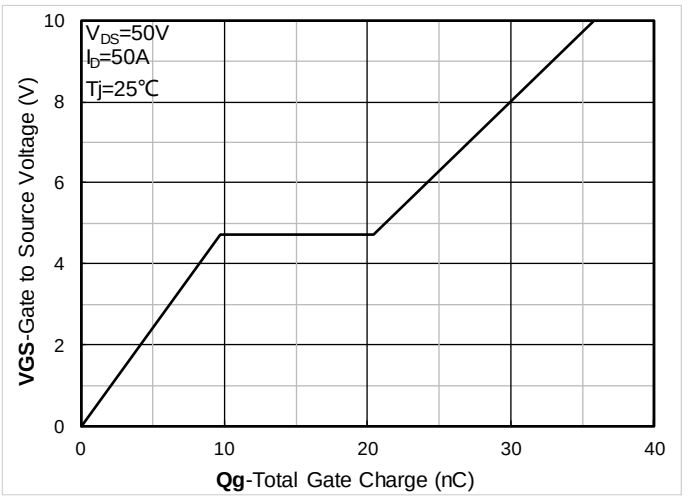


Figure 4. Gate Charge; typical values

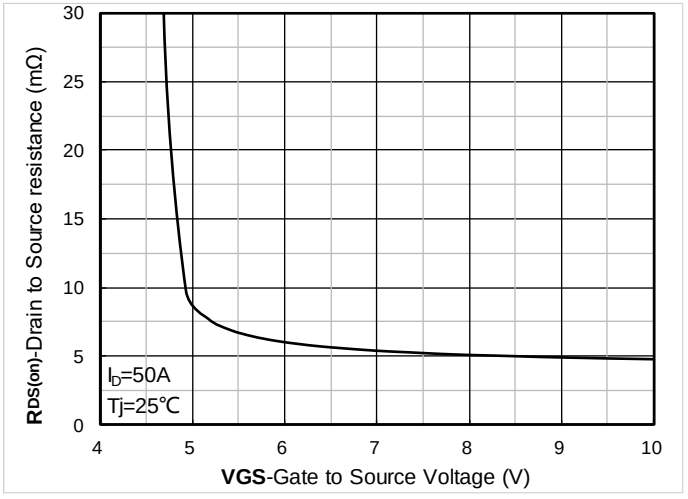


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

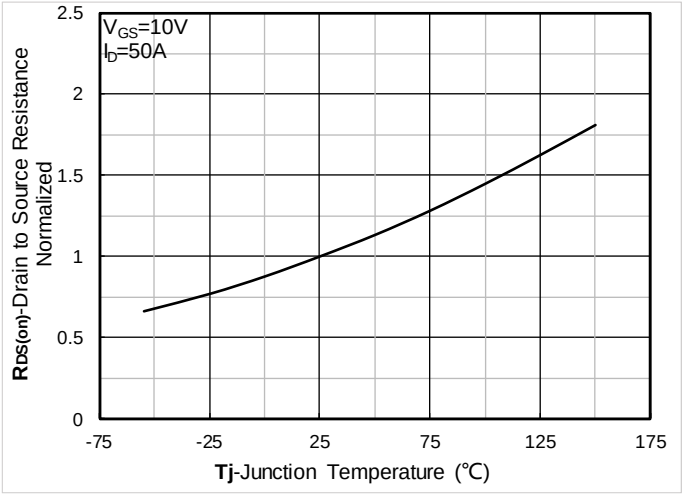


Figure 6. Normalized On-Resistance

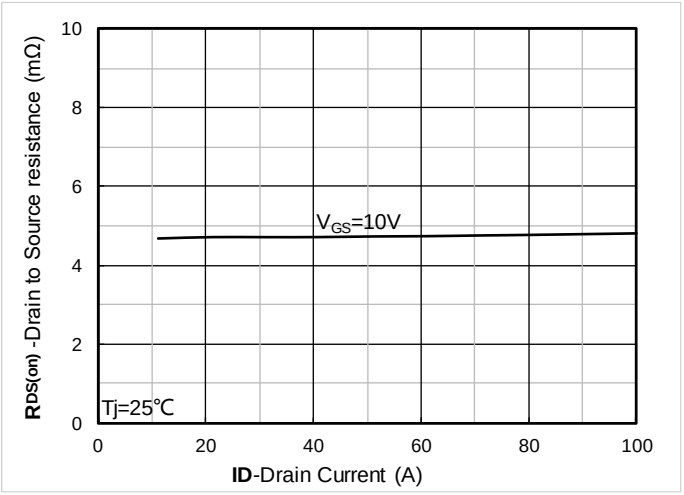


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

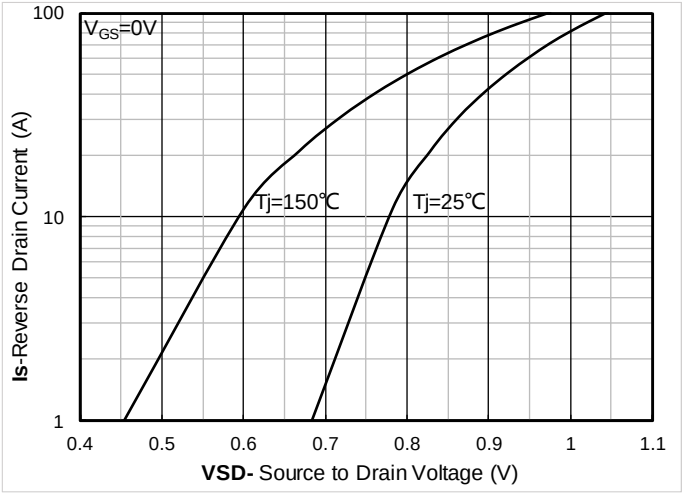


Figure 8. Forward characteristics of reverse diode; typical values

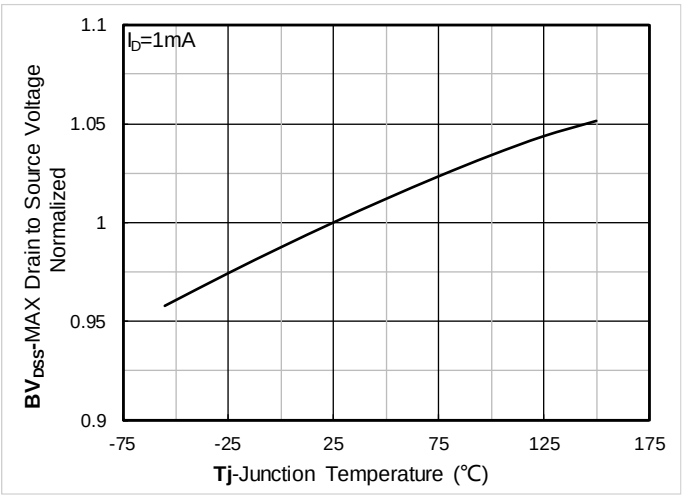


Figure 9. Normalized breakdown voltage

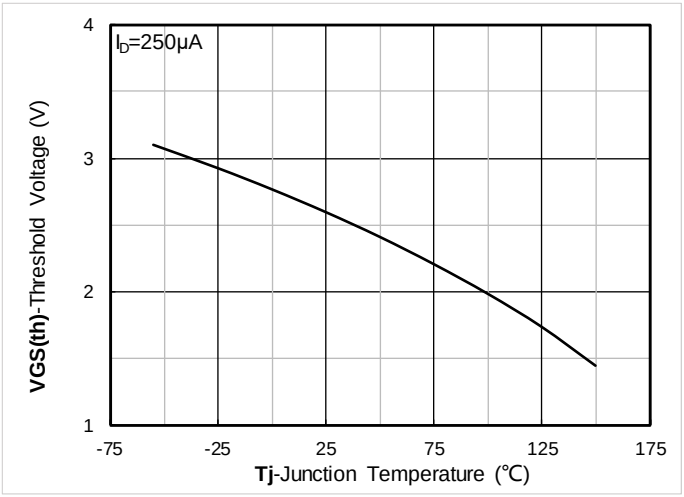


Figure 10. Gate Threshold voltage; typical values

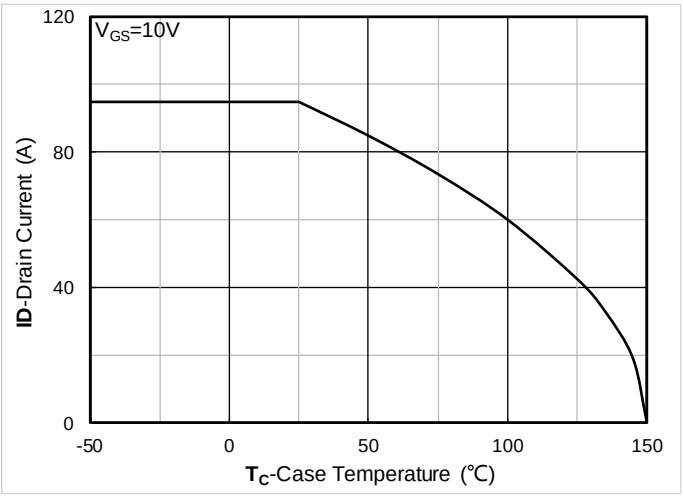


Figure 11. Current dissipation

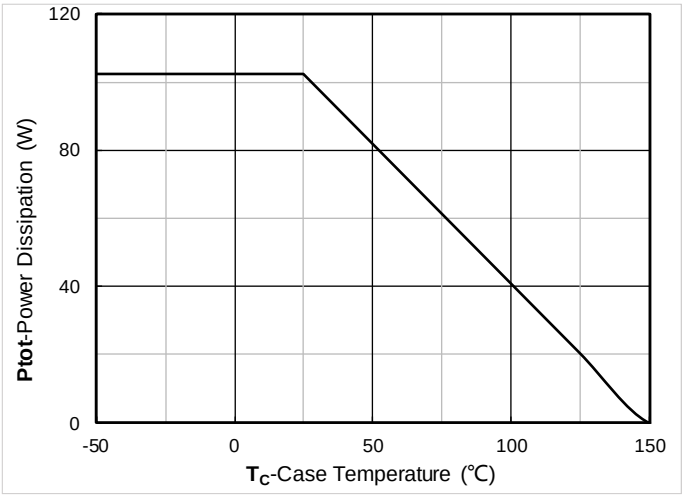


Figure 12. Power dissipation

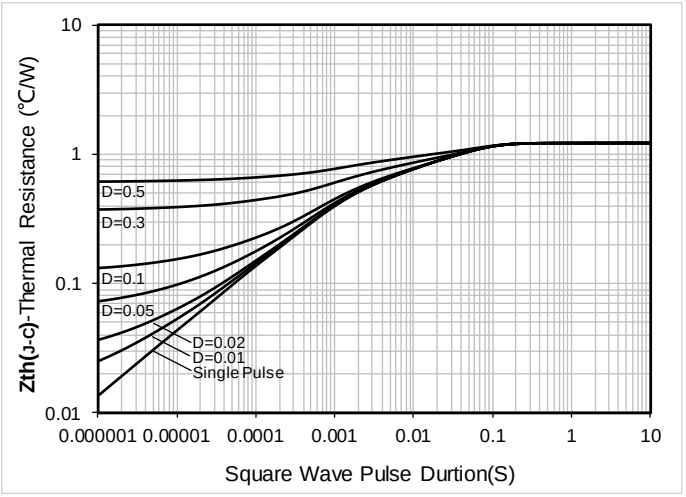


Figure 13. Maximum Transient Thermal Impedance

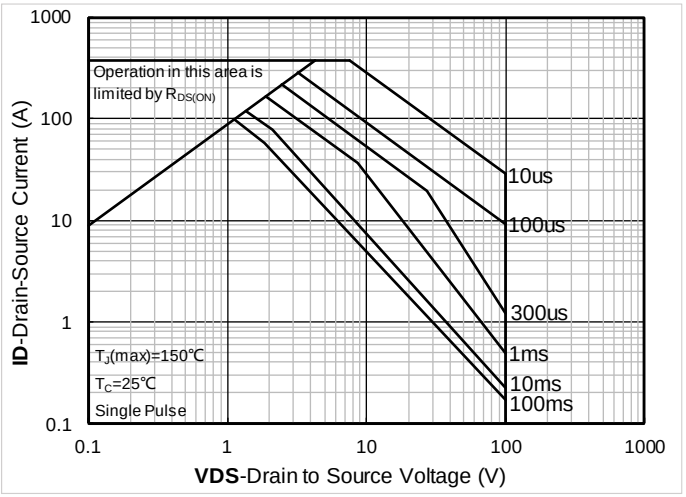
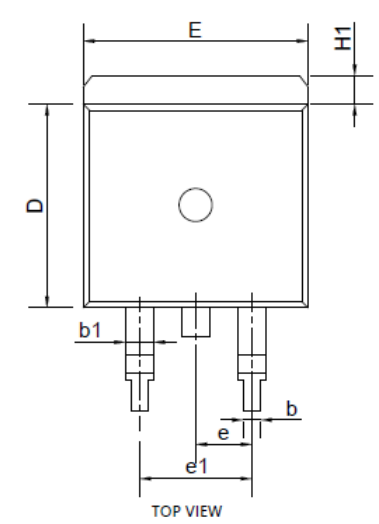
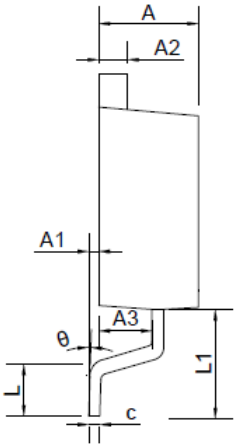


Figure 14. Safe Operation Area

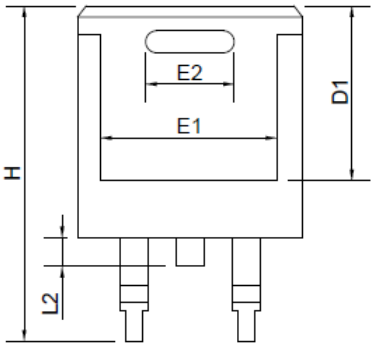
■ TO-263-C Package information



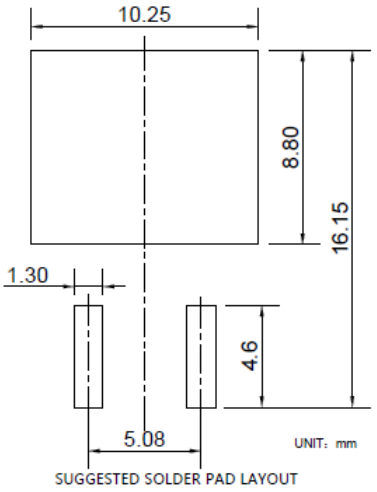
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SUGGESTED SOLDER PAD LAYOUT

DIMENSIONS				
SYMBOL	INCHES		MILLIMETER	
	MIN.	MAX.	MIN.	MAX.
A	0.171	0.183	4.350	4.650
A1	0.000	0.008	0.000	0.200
A2	0.048	0.054	1.220	1.380
A3	0.089	0.100	2.250	2.550
b	0.028	0.035	0.700	0.900
b1	0.046	0.054	1.180	1.380
c	0.017	0.023	0.420	0.580
D	0.356	0.368	9.050	9.350
D1	0.311 REF.		7.900 REF.	
E	0.386	0.403	9.800	10.240
E1	0.302	0.325	7.660	8.260
E2	0.157 REF.		4.000 REF.	
e	0.100 BSC		2.540 BSC	
e1	0.200 BSC		5.080 BSC	
H	0.585	0.608	14.850	15.450
H1	0.043	0.058	1.080	1.480
L	0.080	0.096	2.030	2.430
L2	0.043	0.059	1.100	1.500
θ	0°	8°	0°	8°

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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